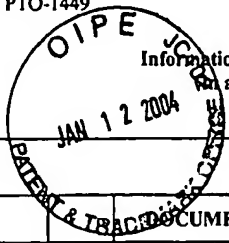
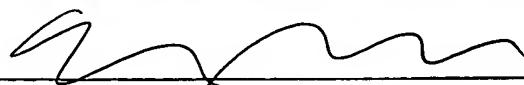


PTO-1449		Application No. 10/663,051		Applicant(s): GORDON MA ET AL.	
		Docket Number 068736.0232		Group Art Unit 2811	Filing Date September 15, 2003

U.S. PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
EL	1	4,811,075	03/07/89	Eklund	357	46	04/24/87
EL	2	5,155,563	10/13/92	Davies et al.	357	23.4	03/18/91
EL	3	5,313,082	05/17/94	Eklund	257	262	02/16/93
EL	4	6,168,983	01/02/01	Rumennik et al.	438	188	02/05/99
EL	5	6,563,171	05/13/03	Disney	257	342	11/12/02

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

NON-PATENT DOCUMENTS			
		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
EL	6	J.A. Appels and H.M.J. Vaes, "High voltage thin layer devices (RESURF devices)", IEDM technical digest, pp. 238-241	1979
EL	7	H.M.J. Vaes and J.A. Appels, "High voltage high current lateral devices", IEDM technical digest, pp. 87-90	1980
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EL	12	J.G. Mena and C.A.T. Salama, "High-voltage multiple-resistivity Drift-Region LDMOS", Solid State Electronics, Vol. 29, No. 6, pp. 647-656	1986
EL	13	M.D. Pocha and R.W. Dutton, "A computer-aided design model for High-Voltage Double Diffused MOS (DMOS) Transistors", IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 5	1976
EL	14	I. Yoshia, M. Katsueda, S. Ohtaka, Y. Maruyama and T. Okabe, "High Efficient 1.5 GHz Si Power MOSFET for Digital Cellular Front End"; Proceedings of International Symposium on Power Semiconductor Devices & ICs; Tokyo, pp. 156-157	1992

EXAMINER	DATE CONSIDERED
	8/28/07

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.